

2N7002

**SURFACE MOUNT
N-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET**



SOT-23 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N7002 type is a N-Channel Field Effect Transistor, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications.

MARKING CODE: 702

MAXIMUM RATINGS: (T_A=25°C)

Drain-Source Voltage
Drain-Gate Voltage
Gate-Source Voltage
Continuous Drain Current (T_C=25°C)
Continuous Drain Current (T_C=100°C)
Continuous Source Current (Body Diode)
Maximum Pulsed Drain Current
Maximum Pulsed Source Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{DS} 60
V_{DG} 60
V_{GS} 40
I_D 115
I_D 75
I_S 115
I_{DM} 800
I_{SM} 800
P_D 350
T_J, T_{stg} -65 to +150
θ_{JA} 357

UNITS

V
V
V
mA
mA
mA
mA
mA
mW
°C
°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{GSSF}	V _{GS} =20V			100	nA
I _{GSSR}	V _{GS} =20V			100	nA
I _{DSS}	V _{DS} =60V, V _{GS} =0			1.0	μA
I _{DSS}	V _{DS} =60V, V _{GS} =0, T _A =125°C			500	μA
I _{D(ON)}	V _{DS} =10V, V _{GS} =10V	500			mA
BV _{DSS}	I _D =10μA	60	105		V
V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	2.1	2.5	V
V _{DS(ON)}	V _{GS} =10V, I _D =500mA			3.75	V
V _{DS(ON)}	V _{GS} =5.0V, I _D =50mA			0.375	V
V _{SD}	V _{GS} =0, I _S =11.5mA			1.5	V
r _{DS(ON)}	V _{GS} =10V, I _D =500mA		3.7	7.5	Ω
r _{DS(ON)}	V _{GS} =10V, I _D =500mA, T _A =100°C			13.5	Ω
r _{DS(ON)}	V _{GS} =5.0V, I _D =50mA		6.2	7.5	Ω
r _{DS(ON)}	V _{GS} =5.0V, I _D =50mA, T _A =100°C			13.5	Ω
g _{FS}	V _{DS} =10V, I _D =200mA	80			mS

R5 (31-January 2011)

2N7002

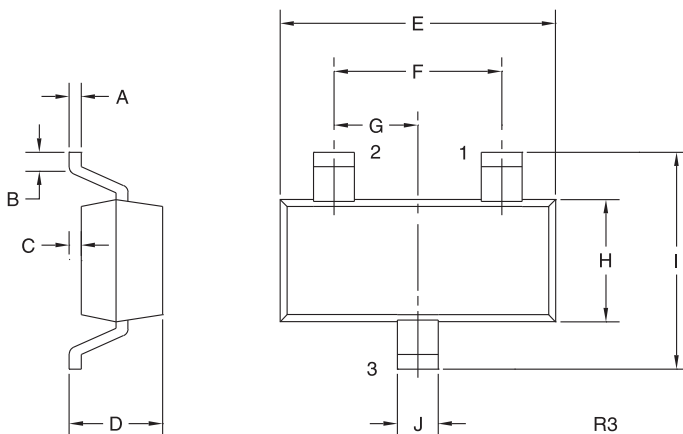
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MAX	UNITS
C_{rss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$	5.0	pF
C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$	50	pF
C_{oss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$	25	pF
t_{on}	$V_{DD}=30\text{V}, I_D=200\text{mA}, R_G=25\Omega, R_L=150\Omega$	20	ns
t_{off}	$V_{DD}=30\text{V}, I_D=200\text{mA}, R_G=25\Omega, R_L=150\Omega$	20	ns

SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Gate
- 2) Source
- 3) Drain

MARKING CODE: 702

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R5 (31-January 2011)

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